

Citations for Target : **GaAs**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1964	Pohlan, C. Lutz, H. Sizmann, R. 'Uberreichweiten Schneller Ionen in Diamantstrukturen' <i>Z. Angew. Phys.</i> , 17, 404-06 (1964) <i>Comment</i> : R, dR. 80 keV Kr -> GaAs (Cryst.)	1964-Pohl 0188
1968	Sattler, A. R. Dearnaley, G. 'Channeling in Diamond-Type and Zinc-Blende Lattices: Comparative Effects in Channeling of Protons and Deuterons in Ge, GaAs, and Si' <i>Phys. Rev.</i> , 161, 244-52 (1967)(Erratum, <i>Phys. Rev.</i> , 165, 750 (1968)) <i>Comment</i> : S. 4-7.6 MeV H, D -> Ge, GaAs, Si (All Cryst.)	1968-Satt 0308
1969	Narayanan, G. H. Spitzer, W. G. 'The Structural Characteristics of Radiation Damage Produced by High Energy (2.7 MeV) Ion Implantation in GaAs' <i>J. Matl. Sci.</i> , 13, 2418-2428 (1978) <i>Comment</i> : R, dR. N, P (2.7 MeV) -> GaAs	1969-Nara 2125
1969	Whitton, J. L. Carter, G. Freeman, J. H. Gard, G. A. 'The Implantation Profiles of 10, 20 and 40 keV 95Kr in Gallium Arsenide' <i>J. Mat. Sci.</i> , 4, 208-17 (1969) <i>Comment</i> : R, dR. 10-40 keV Kr -> GaAs	1969-Whit2 0378
1970	Whitton, J. L. Carter, G. 'The Implantation Profiles of Energetic Heavy Ions in GaAs, GaP, and Ge' <i>W. Palmer, M. W. Thompson, P. D. Townsend: Atomic Collision Phenomena in Solids. North-Holland, Amsterdam, 615-32 (1970)</i> <i>Comment</i> : R, dR. 10-40 keV S, Kr, Na -> GaAs,	1970-Whit 0022
1971	Whitton, J. L. Bellavance, G. R. 'Ion Implantation of Sulphur into GaAs, GaP and Ge Monocrystals' <i>Rad. Effects</i> , 9, 127-31 (1971) <i>Comment</i> : R, dR. 20-40 keV S -> GaAs (Cryst. Axial And Random)	1971-Whit 0681
1972	Carter, G. Baruah, J. N. Grant, W. A. 'The Collection of Ions Implanted in Semiconductors: II: Range Distributions Derived from Collection and Sputter-Etch Curves.' <i>Rad. Effects</i> , 16, 107-114 (1972) <i>Comment</i> : R. 10-30 keV Kr, Tl -> GaAs, GaP, Ge, Si	1972-Cart 0976
1972	Harris, J. S. Harris, J. M. Marcus, H. L. 'Fluorine Ion Implantation Profiles in Gallium Arsenide as Determined by Auger Electron Spectroscopy' <i>Appl. Phys. Letters</i> , 21, 598-600 (1972) <i>Comment</i> : R. 30 keV F -> GaAs	1972-Harr 0997
1972	Mamontov, A. P. Okunev, V. D. Gaman, V. I. Zakharov, B. G. 'Distribution of Radiation Defects in Gallium Arsenide Irradiated with Deuterons' <i>Sov. Phys. Semicond.</i> , 6, 747-749 (1972) <i>Comment</i> : R. 4-12 keV D -> GaAs	1972-Mamo 0998

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1972	Whitton, J. L. Carter, G. Baruah, J. N. Grant, W. A. 'The Collection of Ions Implanted in Semiconductors: I Saturation Effects.' <i>Rad. Effects, 16, 101-105 (1972)</i> <i>Comment : R, dR. 10-30 keV Kr, Tl -> Si, Ge, GaP, GaAs</i>	1972-Whit 0975
1975	Ambridge, T. Heckingbottom, R. 'Effect of Dual Implants into GaAs' <i>Elec. Letters, 11 (1975)</i> <i>Comment : R. 350 keV Se, Ga ->GaAs</i>	1975-Ambr 0957
1975	Lyons, R. P. Ehret, . E. Park, Y. S. 'Ion Implantation of Diatomic Sulpher into GaAs' <i>Bull. Am. Phys. Soc., 20, 318 (1975)</i> <i>Comment : R. About 100 keV S2 -> GaAs.</i>	1975-Lyon 0530
1976	Comas, J. Plew, L. 'Beryllium and Sulfur Ion-Implanted Profiles in GaAs' <i>J. Elec. Mater., 5, 209-221 (1976)</i> <i>Comment : R. 100, 200 keV Be, S -> GaAs</i>	1976-Coma 1021
1976	Comas, J. Plew, L. Chatterjee, P. K. Mclevice, W. V. Vaidyanathan, K. V. 'Impurity Distribution of Ion-Implanted Be in GaAs by Sims, Photoluminescence, and Electrical Profiling' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 141-148 (1976)</i> <i>Comment : R. 250 keV Be -> GaAs</i>	1976-Coma2 1066
1976	Dietrich, H. B. Comas, J. 'Anomalous Redistribution of Ion-Implanted Dopants' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 735-742 (1976)</i> <i>Comment : R. 60 keV Al -> Si, 100 keV Be -> Si, GaAs</i>	1976-Diet 1069
1976	Eisen, F. H. Welch, B. M. 'Radiotracer Profiles in Sulfur Implanted GaAs' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 97-106 (1976)</i> <i>Comment : R. 100 keV 35S -> GaAs</i>	1976-Eise 1065
1976	Harris, T. J. Sealy, B. J. Surrige, R. K. 'Effects of Channelling on the Electrical Properties of Donor Implanted GaAs' <i>Elec. Letters, 12, 664-665 (1976)</i> <i>Comment : R. 90 keV Sn, 90-300 keV Te -> GaAs</i>	1976-Harr 0958

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1976	Kachare, A. H. Spitzer, W. G. Fredrickson, J. E. Euler, F. K. 'Measurements of Layer Thicknesses and Refractive Indices in High Energy Ion Implanted GaAs and GaP' <i>J. Appl. Phys.</i> , 47, 5347-5381 (1976) <i>Comment</i> : R, N, P (3 MeV) -> GaAs, GaP	1976-Kach 2149
1977	Lee, D. H. Malbon, R. M. 'Ion-Implanted Silicon Profiles in GaAs' <i>Appl. Phys. Letters</i> , 30, 327-329 (1977) <i>Comment</i> : R, dR. 50-500 keV Si -> GaAs	1977-Lee 1026
1977	Matsumura, H. Nagatomo, M. Furukawa, S. 'Range of Protons in GaAs' <i>Rad. Effects</i> , 33, 121-123 (1977) <i>Comment</i> : R. 300-500 keV H -> GaAs	1977-Mats 0967
1977	Matsumura, H. Stephens, K. G. 'Electrical Measurement of the Lateral Spread of the Proton Isolation Layer in GaAs' <i>J. Appl. Phys.</i> , 48, 2779-83 (1977). <i>Comment</i> : R, dR, R(Lateral). 300-500 keV H -> GaAs (Conc. Determined By Carrier Removal).	1977-Mats2 0935
1977	Molnar, B. Kennedy, T. A. 'GaAs Ion-Implantation Parameters Studied through Contactless Mobility Measurements' <i>Electrochem. Soc. Extended Abstracts</i> , 261-262, May (1977) <i>Comment</i> : R. 120 keV S -> GaAs	1977-Moln 1059
1977	Surridge, R. K. Sealy, B. J. 'A Comparison of Sn-, Ge-, Se-, and Te-Ion-Implanted GaAs' <i>Appl. Phys.</i> , 10, 911-917 (1977) <i>Comment</i> : R. 200 And 300 keV Sn, Ge, Se, Te -> GaAs	1977-Surr 0955
1977	Surridge, R. K. Sealy, B. J. D'Cruz, A. D. E. Stephens, K. G. 'Annealing Kinetics of Donor Ions Implanted into GaAs' <i>Gallium Arsenide and Related Compounds (Edinburgh)</i> , Ed. by C. Hilsum, 161-167 (1977) <i>Comment</i> : R. 200 keV Se, Sn -> GaAs	1977-Surr2 0956
1977	Surridge, R. K. Sealy, B. J. 'Active Layers for Device Applications by using High-Energy Selenium Implantation into GaAs' <i>Elec. Letters</i> , 13, 233-234 (1977) <i>Comment</i> : R. 150 keV Sn, 1 MeV Se -> GaAs	1977-Surr3 0959
1978	Anderson, W. J. Park, Y. S. 'Flux and Fluence Dependence of Implantation Disorder in GaAs Substrates' <i>J. Appl. Phys.</i> , 49, 4568-4570 (1978) <i>Comment</i> : R, dR. 100 keV Ne, Ar, Kr -> GaAs	1978-Ande3 1216

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1978	Golovchenko, J. A. Venkatesan, T. N. C. 'Annealing of Te-Implanted GaAs by Ruby Laser Irradiation' <i>Appl. Phys. Letters, 32, 147-149 (1978)</i> <i>Comment : R. 50 keV Te -> GaAs</i>	1978-Golo 1099
1978	Muller, G. Haubold, M. Schimko, R. Trapp, M. Schwarz, G. 'Investigations on the Diffusion of Implanted Zinc in GaAs(1-X)P(X) by Ion Microprobe' <i>Phys. Stat. Sol. A, 49, 279-284 (1978)</i> <i>Comment : R. 100 keV Zn -> GaAsP</i>	1978-Mull 1239
1978	Rao, E. V. K. Duhamel, N. Favennec, P. N. L'Haridon, H. 'Investigation of Compensation in Implanted N-GaAs' <i>J. Appl. Phys., 49, 3898-3905 (1978)</i> <i>Comment : R, dR. 200 keV-1 MeV H, B, As -> GaAs</i>	1978-Rao 1215
1978	Shin, B. K. Ehret, J. E. Park, Y. S. Stefiniw, M. 'Dual Implantation of C+ and Ga+ Ions into GaAs' <i>J. Appl. Phys., 49, 2988-2990 (1978)</i> <i>Comment : R. 120 keV Ga, 60 keV C -> GaAs</i>	1978-Shin 1112
1978	Vedmanov, G. D. Neshov, F. G. Puzanov, A. A. Urmanov, A. R. 'Determining Stopping Power from Spectra of Backscattered Ions' <i>Sov. Atom. Energy, 45, 989-991 (1978)</i> <i>Comment : S. N (0.75-7.4MeV) -> Fe, Ge, GaAs, FeGe2</i>	1978-Vedm 1537
1979	Donnelly, J. P. Armiento, C. A. 'Beryllium-Ion Implantation in InP and In(1-X)Ga(X)As(Y)P(1-Y)' <i>Appl. Phys. Letters, 34, 96-99 (1979)</i> <i>Comment : R. 50-400 keV Be -> InP, InGaAsP</i>	1979-Donn 1208
1979	Inada, T. Kato, S. Maeda, Y. Tokunaga, K. 'Doping Profiles in Zn-Implanted GaAs after Laser Annealing' <i>J. Appl. Phys., 50, 6000-6002 (1979)</i> <i>Comment : R, dR. 100 keV Zn -> GaAs</i>	1979-Inad 1297
1979	Kang, S. T. Shimizu, R. Okutani, T. 'Sputtering of Si with keV Ar+ Ions. II. Computer Simulation of Sputter Broadening Due to Ion Bombardment in Depth Profiling.' <i>Jap. J. Appl. Phys., 18, 1987-1994 (1979)</i> <i>Comment : R, dR. 45 keV As -> GaAs</i>	1979-Kang 1337
1979	Kasahara, J. Arai, M. Watanabe, N. 'Suppression of Thermal Conversion in Cr-Doped Semi-Insulating GaAs' <i>J. Appl. Phys., 50, 8229-8231 (1979)</i> <i>Comment : R, dR. 70-130 keV Si -> GaAs</i>	1979-Kasa 1300

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1979	Muller, G. Trapp, M. Schimko, R. Richter, C. E. 'Measurement of Range Distributions of Zinc and Nitrogen Ions in Multiple-Layer Substrates with Secondary Ion Microprobe' <i>Phys. Stat. Sol. A</i> , 51 , 87-92 (1979) <i>Comment</i> : R, dR. 50-300 keV N, Zn -> SiO ₂ -GaAs(1-X)P(X), SiO ₂ -Si ₃ N ₄	1979-Mull 1237
1979	Park, Y. S. Grant, J. T. Haas, T. W. 'The Determination of Sulfur-Ion-Implantation Profiles in GaAs using Auger Electron Spectroscopy' <i>J. Appl. Phys.</i> , 50 , 809-812 (1979) <i>Comment</i> : R, dR. 60, 120 keV S ⁺ , S ₂ ⁺ -> GaAs	1979-Park 1221
1979	Tandon, J. L. Nicolet, M-A. Eisen, F. H. 'Silicon Implantation in GaAs' <i>Appl. Phys. Letters</i> , 34 , 165-167 (1979) <i>Comment</i> : R, dR. 300 keV Si -> GaAs	1979-Tand 1207
1979	Williamson, K. R. Theis, W. M. Yun, S. S. Park, Y. S. Ehret, J. E. 'Glow-Discharge Optical Spectroscopy Measurement of B-, Ge-, and Mg-Implanted GaAs' <i>J. Appl. Phys.</i> , 50 , 8019-8024 (1979) <i>Comment</i> : R, dR. 60-120 keV B, Ge, Mg -> GaAs	1979-Will 1304
1979	Yeo, Y. K. Park, Y. S. Yu, P. W. 'Electrical Measurements and Optical Activation Studies in Mg-Implanted GaAs' <i>J. Appl. Phys.</i> , 50 , 3274-3281 (1979) <i>Comment</i> : R, dR. 120 keV Mg -> GaAs (Cr-Doped)	1979-Yeo 1225
1980	Tashlykov, I. S. 'Backscattering Measurements of P ⁺ Implanted GaAs Crystals' <i>Nucl. Inst. Methods</i> , 170 , 403-406 (1980) <i>Comment</i> : R, dR. 30-60 keV P -> GaAs	1980-Tash 1379
1983	Wilson, R. G. Jamba, D. M. Deline, V. R. Evans, C. A. Park, Y. S. 'Depth Distributions of Sulfur Implanted into GaAs as a Function of Ion Energy, Ion Fluence, and Annealing Temperature and Encapsulation' <i>J. Appl. Phys.</i> , 54 , 3849-3854 (1983) <i>Comment</i> : R. S (40-600 keV) -> GaAs	1983-Wils 2023
1991	Arstila, K. Keinonen, J. Tikkanen, P. 'Stopping Power for Low-Velocity Mg Ions in Si, Ge and GaAs' <i>Phys. Rev. B</i> , 43 , 13967-13970 (1991) <i>Comment</i> : S. Mg (0-0.8 MeV/amu) -> Si, Ge, GaAs	1991-Arst 1910
1994	Kido, Y. Ikeda, A. Yamamoto, Y. Nakata, J. Yamaguchi, H. 'Impact Parameter Dependent Stopping Powers for Axially Channeled and Semi-Channeled MeV He Ions in GaAs:Er' <i>Phys. Rev. B</i> , 49 , 14387-14396 (1994) <i>Comment</i> : S. He (2 MeV) -> GaAs Channeling Effects	1994-Kido 2044

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1994	Raisanen, J. Rauhala, E. 'Ranges of 1.0-2.7 MeV H and He Ions in GaAs' <i>Nucl. Inst. Methods, B93, 1-4 (1994)</i> <i>Comment : R. H, He (1.0-2.7 MeV) -> GaAs</i>	1994-Rais 1129
1996	Misdaq, M. A. Ellassali, R. 'Average Stopping Powers for Channeled Ions using Computational and Experimental Methods' <i>Nucl. Inst. Methods, 119, 325-330 (1996)</i> <i>Comment : S. Light ions -> Si, GaAs (channeled)</i>	1996-Misd 0964
1996	Rajatora, M. Vakevainen, K. Ahlgren, T. Rauhala, E. Raisanen, J. 'Stopping Powers of GaAs for 0.3-2.5 MeV H and He Ions' <i>Nucl. Inst. Methods, B119, 457-462 (1996)</i> <i>Comment : S. H, He (0.3-2.5 MeV) -> GaAs</i>	1996-Raja 2165